

Dual P-Ch 30V Fast Switching MOSFETs

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Description

The XR4803A is the high cell density trench P-ch MOSFETs, which provide excellent $R_{DS(on)}$ and gate charge for most of the synchronous buck converter applications.

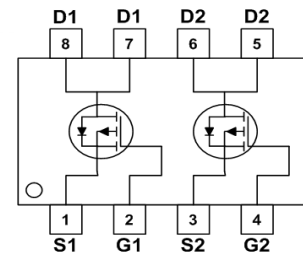
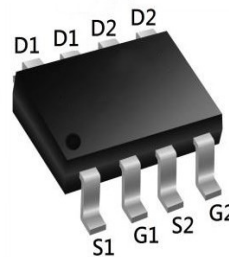
The XR4803A meet the RoHS and Green Product

Product Summary



BVDSS	$R_{DS(on)}$	I_D
-30V	35mΩ	-5.3A

SOP8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	-5.3	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	-4.3	A
I_{DM}	Pulsed Drain Current ²	-20	A
EAS	Single Pulse Avalanche Energy ³	---	mJ
I_{AS}	Avalanche Current	---	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	2.0	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	100	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	---	$^\circ C/W$

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Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = -250μA	-30	-	-	V
Gate-body Leakage current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V	-	-	-1	μA
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.5	-2.1	V
Drain-Source On-Resistance ³	R _{DS(on)}	V _{GS} = -10V, I _D = -4.1A	-	35	55	mΩ
		V _{GS} = -4.5V, I _D = -3A	-	52	85	
Dynamic Characteristics ⁴						
Input Capacitance	C _{iss}	V _{DS} = -15V, V _{GS} =0V, f =1MHz	-	530	-	pF
Output Capacitance	C _{oss}		-	70	-	
Reverse Transfer Capacitance	C _{rss}		-	56	-	
Switching Characteristics ⁴						
Total Gate Charge	Q _g	V _{GS} = -10V,I _D = -4.1A, V _{DS} = -15V	-	10	-	nC
Gate-Source Charge	Q _{gs}		-	2	-	
Gate-Drain Charge	Q _{gd}		-	2.8	-	
Turn-On Delay Time	t _{d(on)}	V _{GS} = -10V ,V _{DD} = -15V, ,R _{GEN} = 6Ω, I _D = -4.1A,	-	6.9	-	ns
Rise Time	t _r		-	12	-	
Turn-Off Delay Time	t _{d(off)}		-	19	-	
Fall Time	t _f		-	7.5	-	
Source-Drain Body Diode Characteristics						
Diode Forward Voltage ³	V _{SD}	I _S = -1.7A, V _{GS} = 0V	-	-	-1.2	V
Continuous Source Current	I _S		-	-	-5.3	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$.
2. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

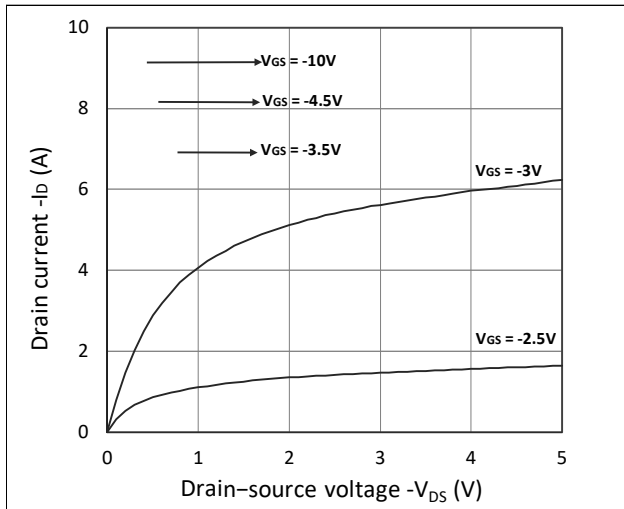


Figure 1. Output Characteristics

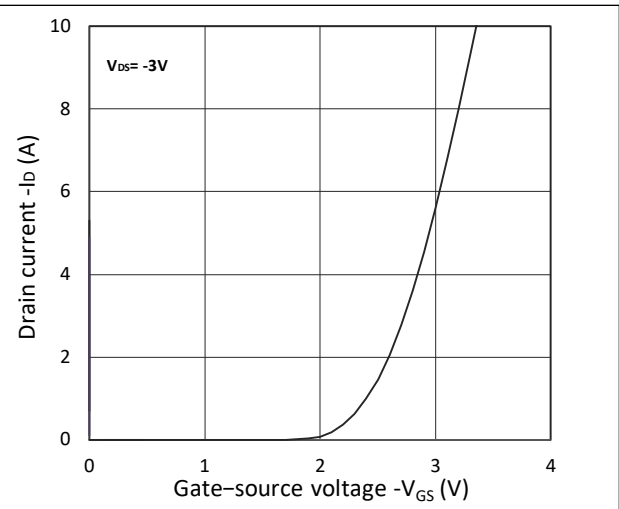


Figure 2. Transfer Characteristics

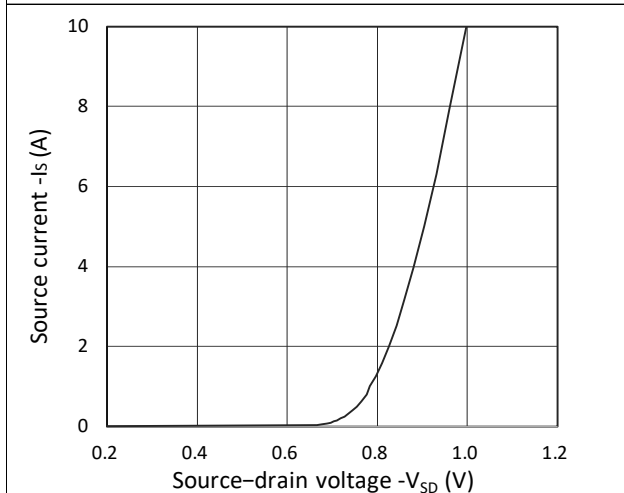


Figure 3. Forward Characteristics of Reverse

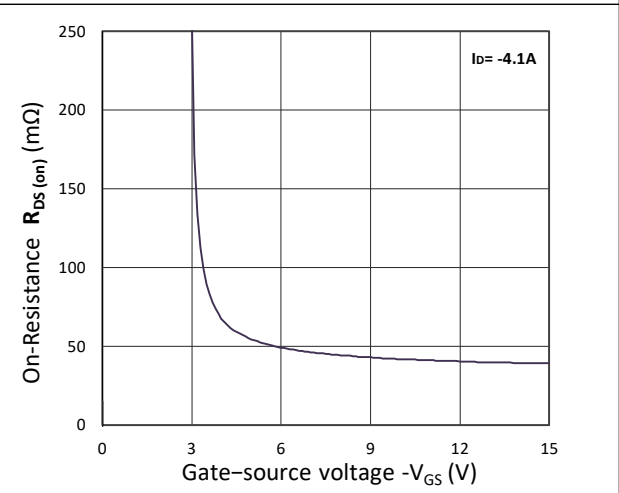


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

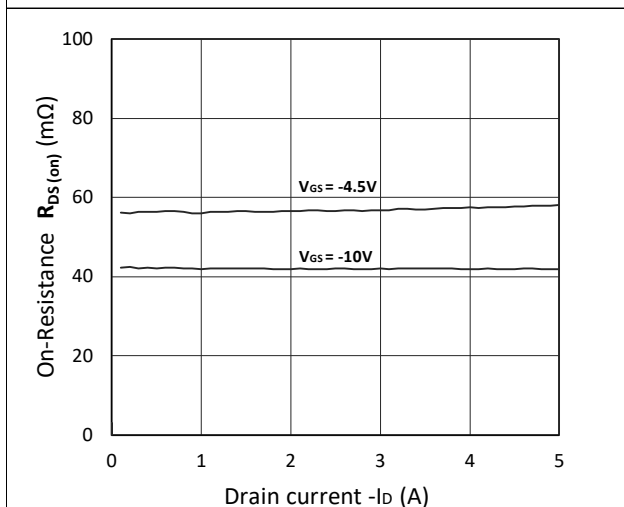


Figure 5. $R_{DS(ON)}$ vs. I_D

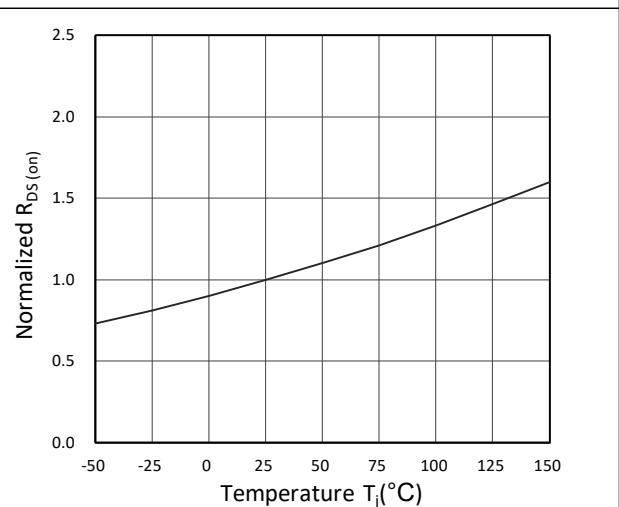


Figure 6. Normalized $R_{DS(ON)}$ vs. Temperature

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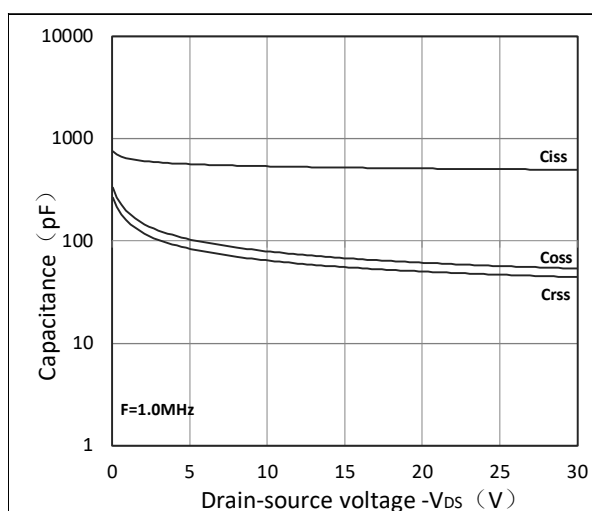


Figure 7. Capacitance Characteristics

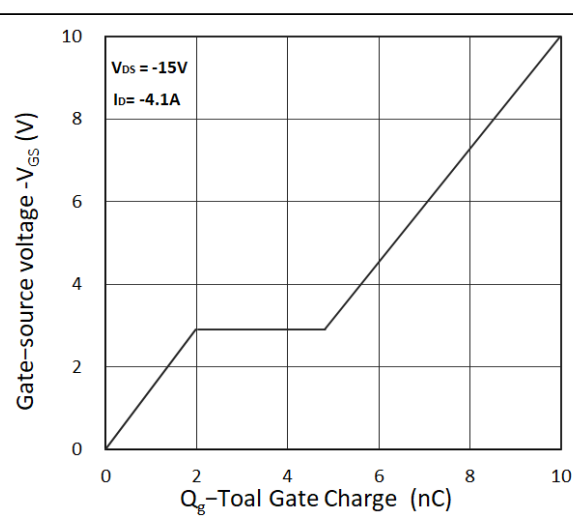
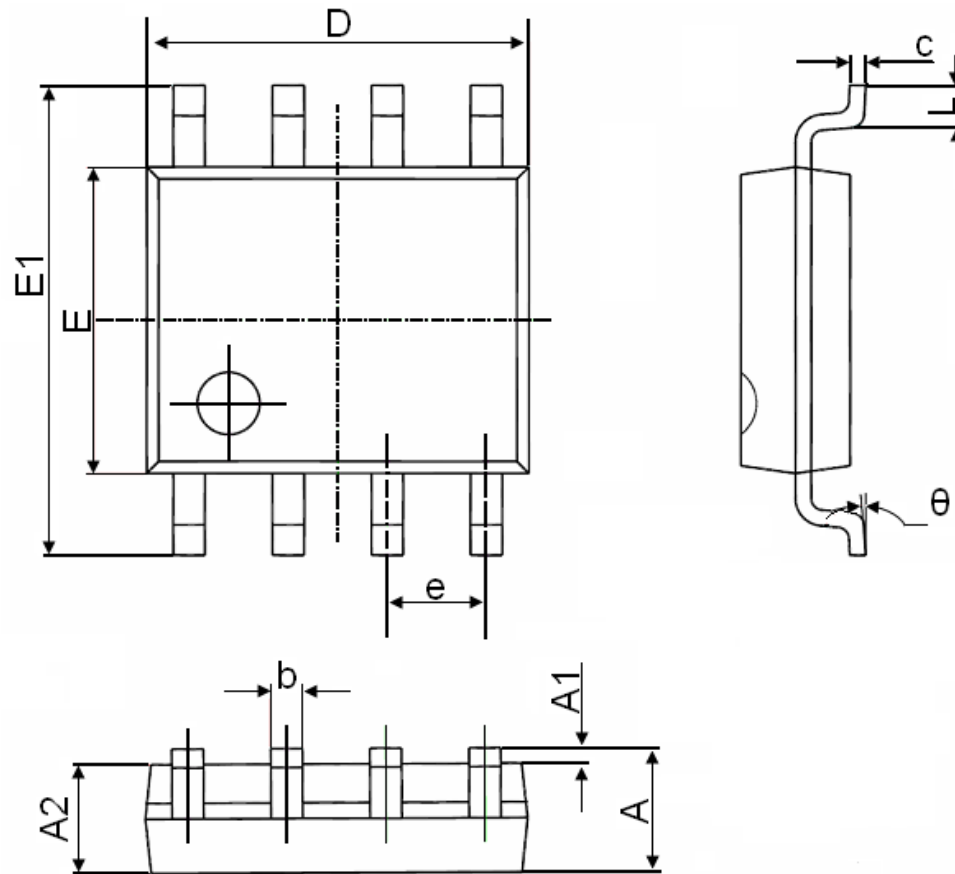


Figure 8. Gate Charge Characteristics

Package Mechanical Data- SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°